



TMG130N10HNF

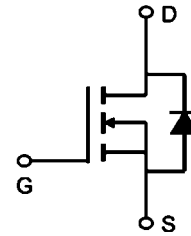
N-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 100V$ $I_D = 130A$</p> <p>$R_{DS(ON)} = 3.7m\Omega$ (typ.) @ $V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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NF:DFN5x6-8L



Marking: G130N10



Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25^\circ C$	130
		$T_C = 100^\circ C$	76
Pulsed Drain Current ¹	I_{DM}	480	A
Single Pulse Avalanche Energy ²	EAS	320	mJ
Total Power Dissipation	P_D	131.6	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	48	$^\circ C/W$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	0.95	$^\circ C/W$

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Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	-	-	V	
Gate-body Leakage current	I_{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 100V, V _{GS} = 0V	T _J = 25°C	-	-	1	μA
			T _J = 100°C	-	-	100	
Gate-Threshold Voltage	V_{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V	
Drain-Source on-Resistance ⁴	R_{DS(on)}	V _{GS} = 10V, I _D = 20A	-	3.7	4.5	mΩ	
Forward Transconductance ⁴	g_{fs}	V _{DS} = 10V, I _D = 20A	-	62	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C_{iss}	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz	-	6865	-	pF	
Output Capacitance	C_{oss}		-	740	-		
Reverse Transfer Capacitance	C_{rss}		-	21	-		
Gate Resistance	R_g	f = 1MHz	-	1.3	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q_g	V _{GS} = 10V, V _{DS} = 50V, I _D = 20A	-	112.5	-	nC	
Gate-Source Charge	Q_{gs}		-	30.5	-		
Gate-Drain Charge	Q_{gd}		-	27.3	-		
Turn-on Delay Time	t_{d(on)}	V _{GS} = 10V, V _{DD} = 50V, R _G = 3Ω, I _D = 20A	-	33	-	ns	
Rise Time	t_r		-	39	-		
Turn-off Delay Time	t_{d(off)}		-	67.1	-		
Fall Time	t_f		-	32	-		
Body Diode Reverse Recovery Time	t_{rr}	I _F = 20A, dI/dt = 100A/μs	-	58.7	-	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	97.3	-	nC	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V_{SD}	I _F = 20A, V _{GS} = 0V	-	-	1.2	V	
Continuous Source Current	I_s	T _C = 25°C	-	-	130	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The EAS data shows Max. rating. The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.4mH, I_{AS} = 40A
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..



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Typical Characteristics

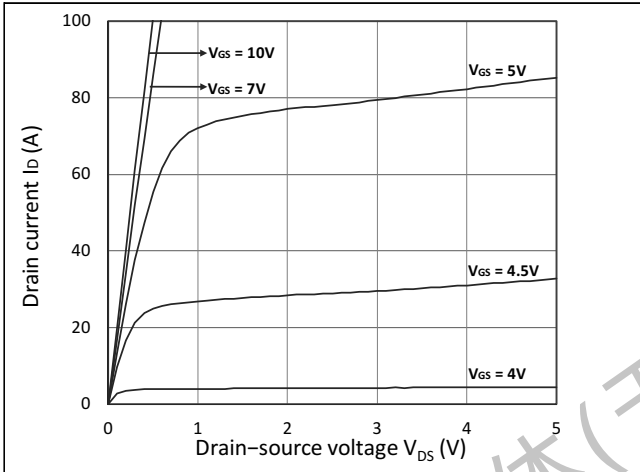


Figure 1. Output Characteristics

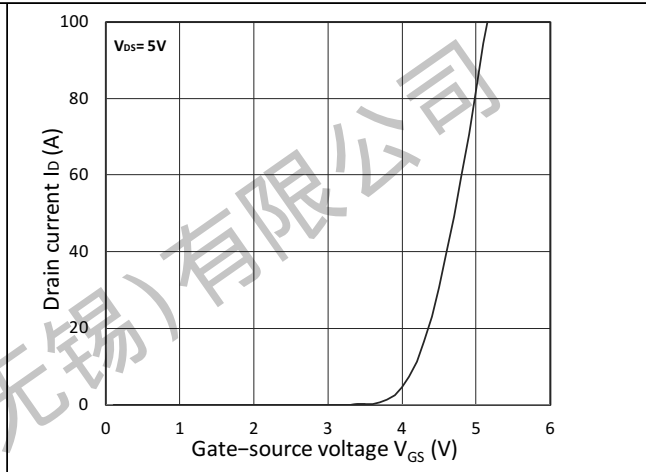


Figure 2. Transfer Characteristics

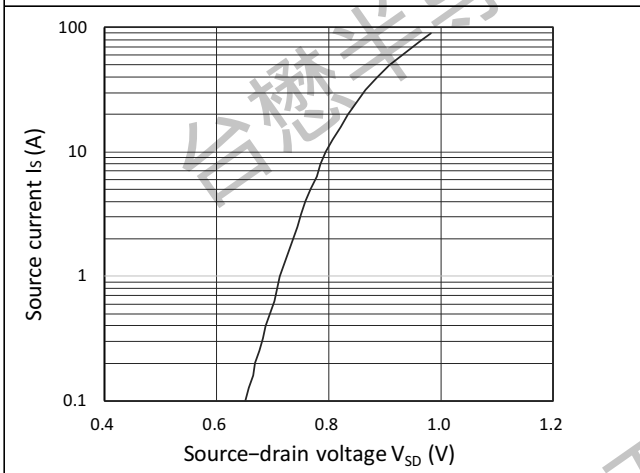


Figure 3. Forward Characteristics of Reverse

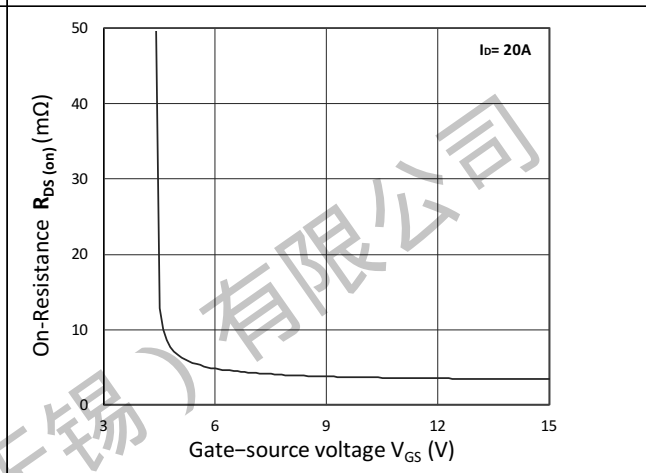


Figure 4. $R_{DS(on)}$ vs. V_{GS}

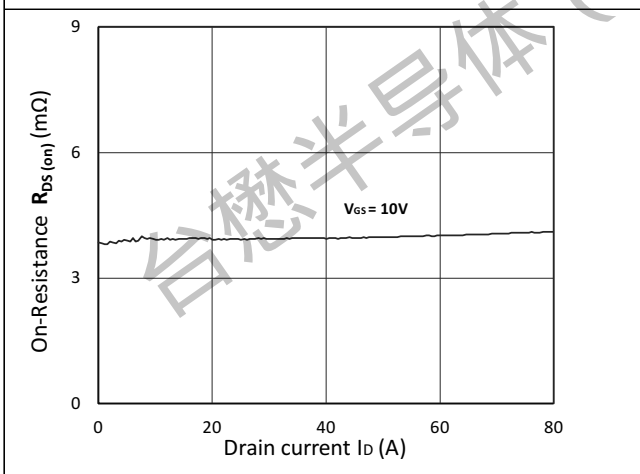


Figure 5. $R_{DS(on)}$ vs. I_D

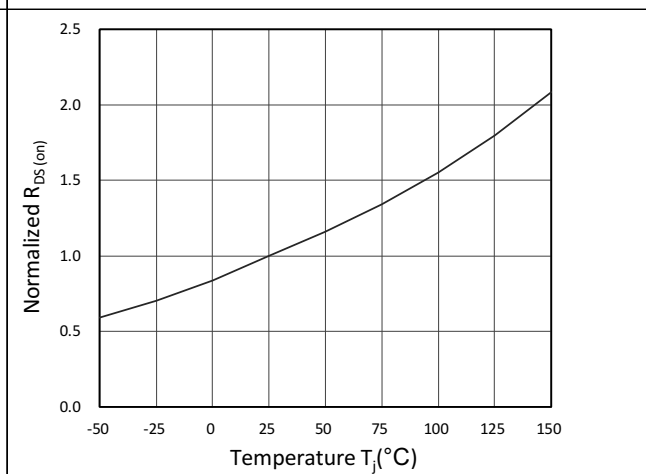


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

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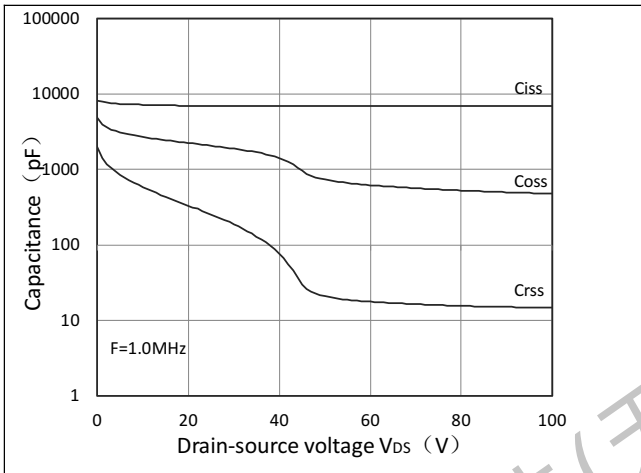


Figure 7. Capacitance Characteristics

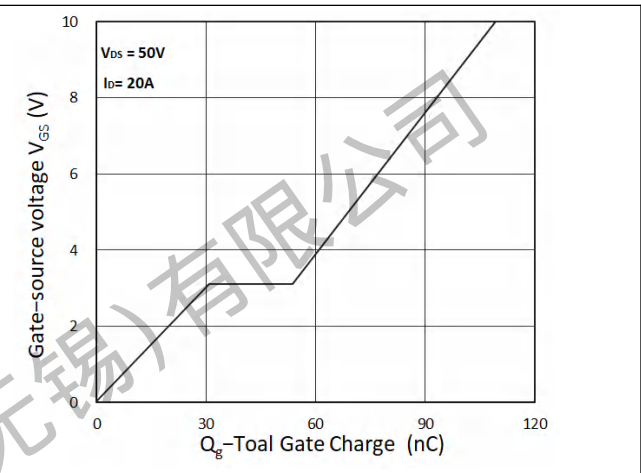


Figure 8. Gate Charge Characteristics

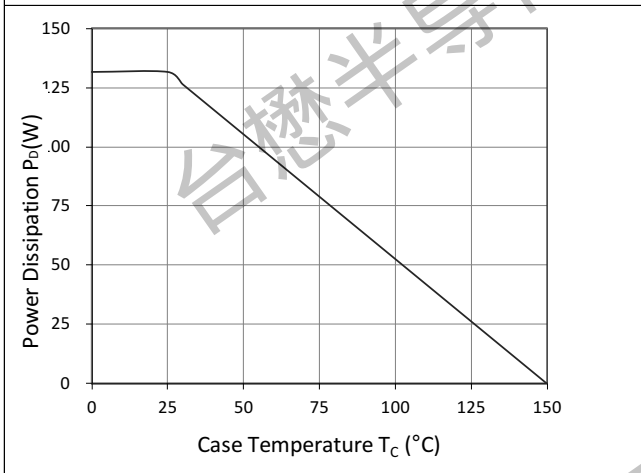


Figure 9. Power Dissipation

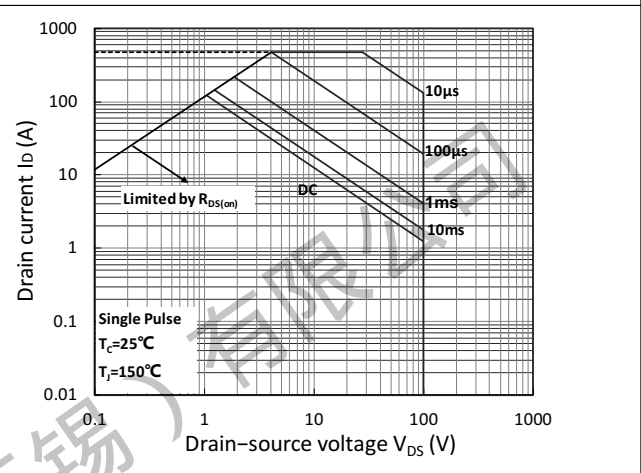


Figure 10. Safe Operating Area

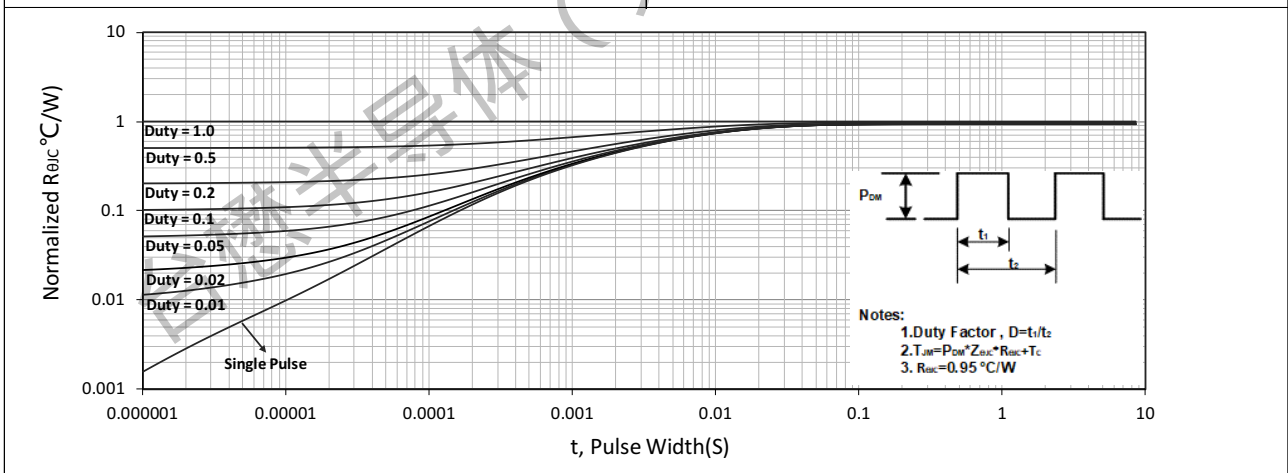


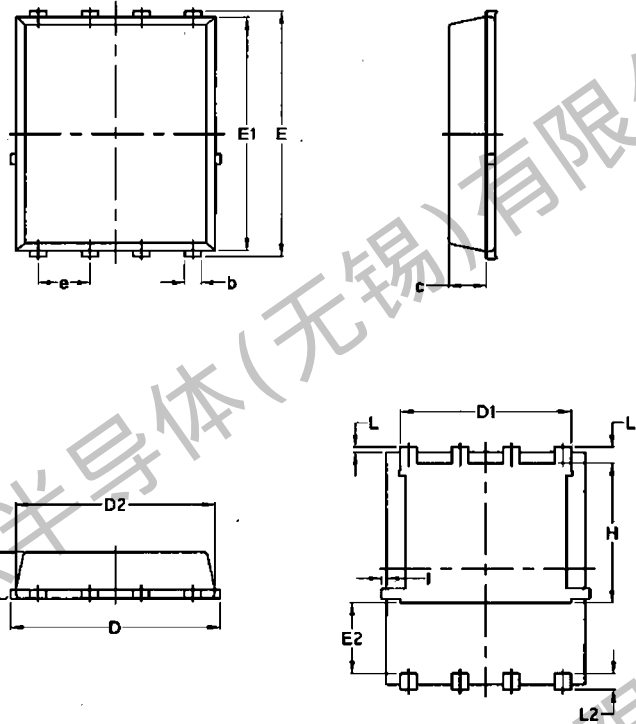
Figure 11. Normalized Maximum Transient Thermal Impedance



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Package Mechanical Data:DFN5x6-8L

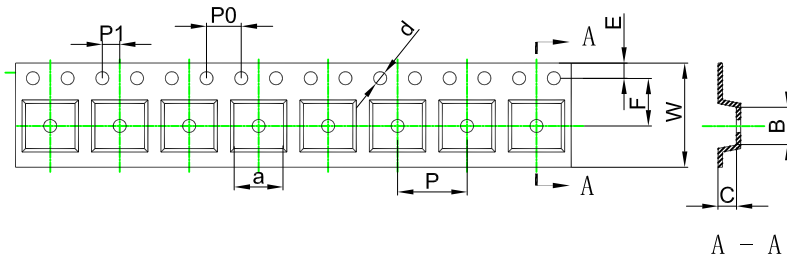


Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

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PDFN5x6-8L Embossed Carrier Tape



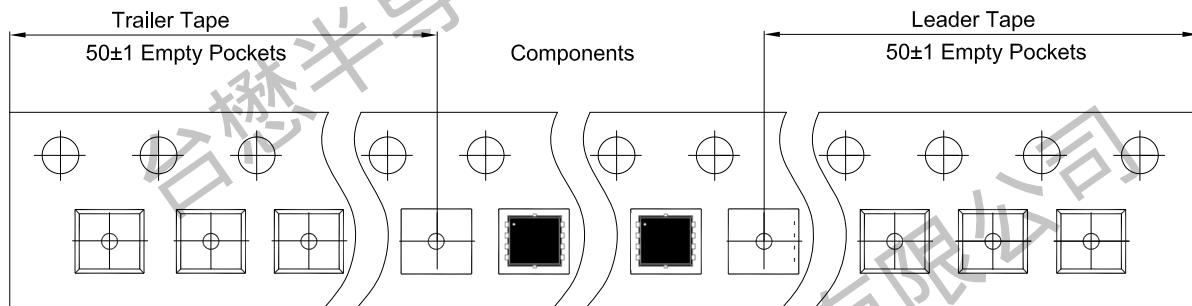
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

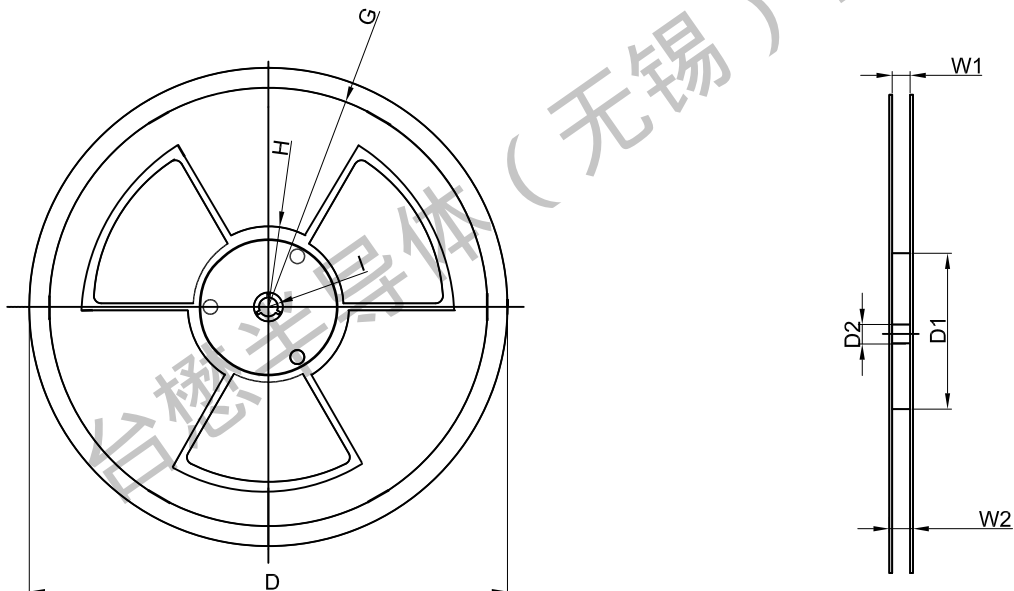
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN5x6-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5x6-8L Tape Leader and Trailer



PDFN5x6-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13" Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	



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Revision history:

Date	Rev	Description	Page
2023.04.17	23.04	Original	